

NLSX4373

2-Bit 20 Mb/s Dual-Supply Level Translator

The NLSX4373 is a 2-bit configurable dual-supply bidirectional auto sensing translator that does not require a directional control pin. The V_{CC} I/O and V_L I/O ports are designed to track two different power supply rails, V_{CC} and V_L respectively. The V_{CC} supply rail is configurable from 1.5 V to 5.5 V while V_L supply rail is configurable to 1.5 V to 5.5 V. This allows voltage logic signals on the V_L side to be translated into lower, higher or equal value voltage logic signals on the V_{CC} side, and vice-versa.

The NLSX4373 translator has open-drain outputs with integrated 10 k Ω pullup resistors on the I/O lines. The integrated pullup resistors are used to pullup the I/O lines to either V_L or V_{CC} . The NLSX4373 is an excellent match for open-drain applications such as the I²C communication bus.

Features

- V_L can be Less than, Greater than or Equal to V_{CC}
- Wide V_{CC} Operating Range: 1.5 V to 5.5 V
Wide V_L Operating Range: 1.5 V to 5.5 V
- High-Speed with 20 Mb/s Guaranteed Data Rate
- Low Bit-to-Bit Skew
- Enable Input and I/O Lines have Overvoltage Tolerant (OVT) to 5.5 V
- Nonpreferential Powerup Sequencing
- Integrated 10 k Ω Pullup Resistors
- Small packaging: UDFN8, SO-8, Micro8
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable*
- This is a Pb-Free Device

Typical Applications

- I²C, SMBus, PMBus
- Low Voltage ASIC Level Translation
- Mobile Phones, PDAs, Cameras

Important Information

- ESD Protection for All Pins
 - Human Body Model (HBM) > 7000 V



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MARKING DIAGRAMS



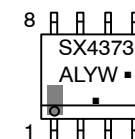
UDFN8
MU SUFFIX
CASE 517AJ



VF = Specific Device Code
M = Date Code
▪ = Pb-Free Package



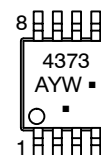
SO-8
D SUFFIX
CASE 751



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package



Micro8™
DM SUFFIX
CASE 846A



A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package

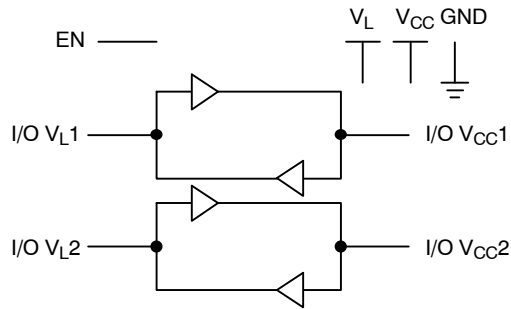
ORDERING INFORMATION

Device	Package	Shipping†
NLSX4373MUTAG	UDFN8 (Pb-Free)	3000/Tape & Reel
NLVX4373MUTAG*	UDFN8 (Pb-Free)	3000/Tape & Reel
NLSX4373DR2G	SO-8 (Pb-Free)	2500/Tape & Reel
NLVX4373DR2G*	SO-8 (Pb-Free)	2500/Tape & Reel
NLSX4373DMR2G	Micro8 (Pb-Free)	4000/Tape & Reel

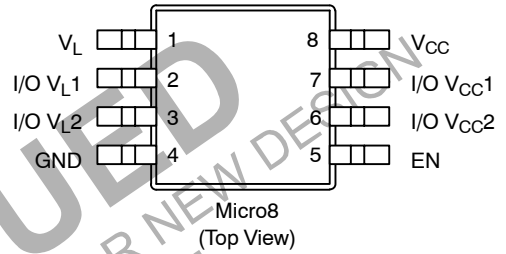
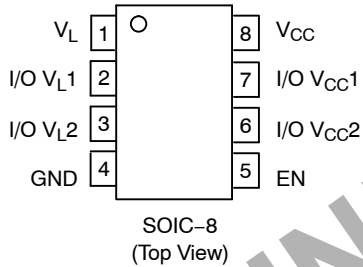
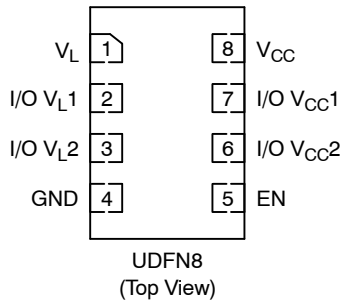
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NLSX4373

LOGIC DIAGRAM



PIN ASSIGNMENTS



PIN ASSIGNMENT

Pins	Description
V _{CC}	V _{CC} Input Voltage
V _L	V _L Input Voltage
GND	Ground
EN	Output Enable
I/O V _{CCn}	V _{CC} I/O Port, Referenced to V _{CC}
I/O V _{Ln}	V _L I/O Port, Referenced to V _L

FUNCTION TABLE

EN	Operating Mode
L	Hi-Z
H	I/O Buses Connected

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V_{CC}	High-side DC Supply Voltage	-0.3 to +7.0		V
V_L	High-side DC Supply Voltage	-0.3 to +7.0		V
I/O V_{CC}	V_{CC} -Referenced DC Input/Output Voltage	-0.3 to ($V_{CC} + 0.3$)		V
I/O V_L	V_L -Referenced DC Input/Output Voltage	-0.3 to ($V_L + 0.3$)		V
V_{EN}	Enable Control Pin DC Input Voltage	-0.3 to +7.0		V
I_{I/O_SC}	Short-Circuit Duration (I/O V_L and I/O V_{CC} to GND)	40	Continuous	mA
T_{STG}	Storage Temperature	-65 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	High-side Positive DC Supply Voltage	1.5	5.5	V
V_L	High-side Positive DC Supply Voltage	1.5	5.5	V
V_{EN}	Enable Control Pin Voltage	GND	5.5	V
V_{IO}	Enable Control Pin Voltage	GND	5.5	V
T_A	Operating Temperature Range	-40	+85	°C

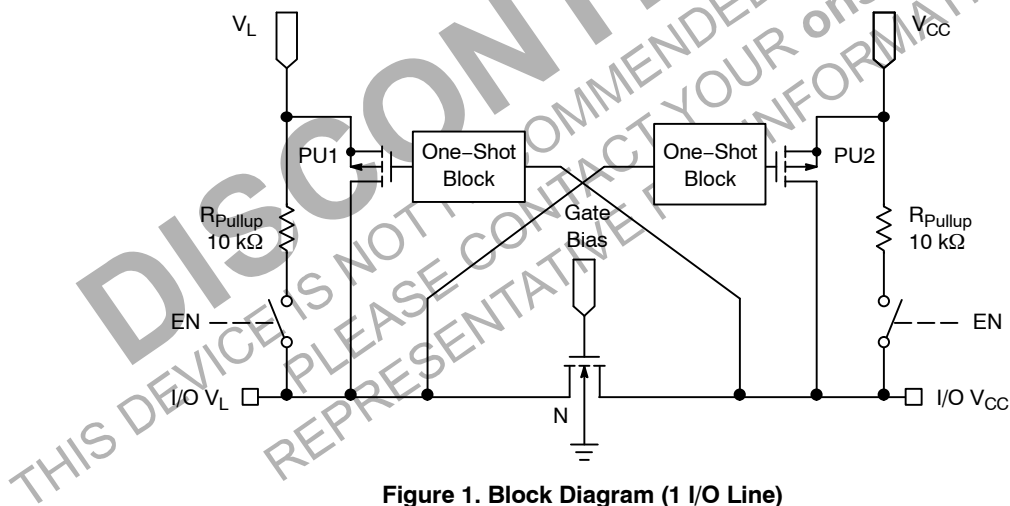


Figure 1. Block Diagram (1 I/O Line)

NLSX4373

DC ELECTRICAL CHARACTERISTICS ($V_{CC} = 1.5\text{ V}$ to 5.5 V and $V_L = 1.5\text{ V}$ to 5.5 V , unless otherwise specified)

Symbol	Parameter	Test Conditions	-40°C to +85°C			Unit
			Min	Typ (Notes 1, 2)	Max	
V_{IHC}	I/O V_{CC} Input HIGH Voltage		$V_{CC} - 0.4$	–	–	V
V_{ILC}	I/O V_{CC} Input LOW Voltage		–	–	0.15	V
V_{IHL}	I/O V_L Input HIGH Voltage		$V_L - 0.2$	–	–	V
V_{ILL}	I/O V_L Input LOW Voltage		–	–	0.15	V
V_{IH}	Control Pin Input HIGH Voltage		$V_L - 0.2$	–	–	V
V_{IL}	Control Pin Input LOW Voltage		–	–	0.15	V
V_{OHC}	I/O V_{CC} Output HIGH Voltage	I/O V_{CC} Source Current = 20 μA	$2/3 * V_{CC}$	–	–	V
V_{OLC}	I/O V_{CC} Output LOW Voltage	I/O V_{CC} Sink Current = 20 μA	–	–	$1/3 * V_{CC}$	V
V_{OHL}	I/O V_L Output HIGH Voltage	I/O V_L Source Current = 20 μA	$2/3 * V_L$	–	–	V
V_{OLL}	I/O V_L Output LOW Voltage	I/O V_L Sink Current = 20 μA	–	–	$1/3 * V_L$	V
I_{QVCC}	V_{CC} Supply Current	I/O V_{CC} and I/O V_L Unconnected, $V_{EN} = V_L$	–	0.5	2.0	μA
I_{QVL}	V_L Supply Current	I/O V_{CC} and I/O V_L Unconnected, $V_{EN} = V_L$	–	0.3	1.5	μA
I_{TS-VCC}	V_{CC} Tristate Output Mode Supply Current	I/O V_{CC} and I/O V_L Unconnected, $V_{EN} = \text{GND}$	–	0.1	1.0	μA
I_{TS-VL}	V_L Tristate Output Mode Supply Current	I/O V_{CC} and I/O V_L Unconnected, $V_{EN} = \text{GND}$	–	0.1	1.0	μA
I_{OZ}	I/O Tristate Output Mode Leakage Current	$T_A = +25^\circ\text{C}$	–	0.1	1.0	μA
R_{PU}	Pullup Resistor I/O V_L and V_{CC}	$T_A = +25^\circ\text{C}$	–	10	–	$\text{k}\Omega$

1. Typical values are for $V_{CC} = +2.8\text{ V}$, $V_L = +1.8\text{ V}$ and $T_A = +25^\circ\text{C}$.
2. All units are production tested at $T_A = +25^\circ\text{C}$. Limits over the operating temperature range are guaranteed by design.

TIMING CHARACTERISTICS – RAIL-TO-RAIL DRIVING CONFIGURATIONS(I/O test circuit of Figures 2 and 3, $C_{LOAD} = 15 \text{ pF}$, driver output impedance $\leq 50 \Omega$, $R_{LOAD} = 1 \text{ M}\Omega$)

Symbol	Parameter	Test Conditions	–40°C to +85°C (Notes 3 and 4)			Unit
			Min	Typ	Max	
V _L = 1.5 V, V _{CC} = 5.5 V						
t _{RVCC}	I/O V _{CC} Risetime				15	ns
t _{FVCC}	I/O V _{CC} Falltime				20	ns
t _{RVL}	I/O V _L Risetime				30	ns
t _{FVL}	I/O V _L Falltime				10	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V _L)				20	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V _{CC})				20	ns
t _{PPSKEW}	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s

 $V_L = 1.8 \text{ V}$, $V_{CC} = 2.8 \text{ V}$

t_{RVCC}	I/O V_{CC} Risettime				15	ns
t_{FVCC}	I/O V_{CC} Falltime				15	ns
t_{RVL}	I/O V_L Risettime				25	ns
t_{FVL}	I/O V_L Falltime				10	ns
$t_{PDVL-VCC}$	Propagation Delay (Driving I/O V_L)				15	ns
$t_{PDVCC-VL}$	Propagation Delay (Driving I/O V_{CC})				15	ns
t_{PPSKEW}	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s

 $V_L = 2.5 \text{ V}$, $V_{CC} = 3.6 \text{ V}$

t_{RVCC}	I/O V_{CC} Risettime				15	ns
t_{FVCC}	I/O V_{CC} Falltime				10	ns
t_{RVL}	I/O V_L Risettime				15	ns
t_{FVL}	I/O V_L Falltime				10	ns
$t_{PDVL-VCC}$	Propagation Delay (Driving I/O V_L)				15	ns
$t_{PDVCC-VL}$	Propagation Delay (Driving I/O V_{CC})				15	ns
t_{PPSKEW}	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s

 $V_L = 2.8 \text{ V}$, $V_{CC} = 1.8 \text{ V}$

t_{RVCC}	I/O V_{CC} Risettime				25	ns
t_{FVCC}	I/O V_{CC} Falltime				10	ns
t_{RVL}	I/O V_L Risettime				20	ns
t_{FVL}	I/O V_L Falltime				15	ns
$t_{PDVL-VCC}$	Propagation Delay (Driving I/O V_L)				15	ns
$t_{PDVCC-VL}$	Propagation Delay (Driving I/O V_{CC})				15	ns
t_{PPSKEW}	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s

3. Typical values are for $V_{CC} = +3.3 \text{ V}$, $V_L = +1.8 \text{ V}$ and $T_A = +25^\circ\text{C}$.4. All units are production tested at $T_A = +25^\circ\text{C}$. Limits over the operating temperature range are guaranteed by design.

TIMING CHARACTERISTICS – RAIL-TO-RAIL DRIVING CONFIGURATIONS(I/O test circuit of Figures 2 and 3, $C_{LOAD} = 15 \text{ pF}$, driver output impedance $\leq 50 \Omega$, $R_{LOAD} = 1 \text{ M}\Omega$)

Symbol	Parameter	Test Conditions	-40°C to +85°C (Notes 3 and 4)			Unit
			Min	Typ	Max	
V _L = 3.6 V, V _{CC} = 2.5 V						
t _{RVCC}	I/O V _{CC} Risetime				15	ns
t _{FVCC}	I/O V _{CC} Falltime				10	ns
t _{RVL}	I/O V _L Risetime				15	ns
t _{FVL}	I/O V _L Falltime				15	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V _L)				15	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V _{CC})				15	ns
t _{PPSKEW}	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s

 $V_L = 5.5 \text{ V}$, $V_{CC} = 1.5 \text{ V}$

t_{RVCC}	I/O V_{CC} Risettime				30	ns
t_{FVCC}	I/O V_{CC} Falltime				10	ns
t_{RVL}	I/O V_L Risettime				15	ns
t_{FVL}	I/O V_L Falltime				20	ns
$t_{PDVL-VCC}$	Propagation Delay (Driving I/O V_L)				20	ns
$t_{PDVCC-VL}$	Propagation Delay (Driving I/O V_{CC})				20	ns
t_{PPSKEW}	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s

3. Typical values are for $V_{CC} = +3.3 \text{ V}$, $V_L = +1.8 \text{ V}$ and $T_A = +25^\circ\text{C}$.4. All units are production tested at $T_A = +25^\circ\text{C}$. Limits over the operating temperature range are guaranteed by design.**TIMING CHARACTERISTICS – OPEN DRAIN DRIVING CONFIGURATIONS**(I/O test circuit of Figures 4 and 5, $C_{LOAD} = 15 \text{ pF}$, driver output impedance $\leq 50 \Omega$, $R_{LOAD} = 1 \text{ M}\Omega$)

Symbol	Parameter	Test Conditions	-40°C to +85°C (Notes 5 and 6)			Unit
			Min	Typ	Max	
+1.5 ≤ V _L ≤ V _{CC} ≤ +5.5 V						
t _{RVCC}	I/O V _{CC} Risettime				400	ns
t _{FVCC}	I/O V _{CC} Falltime				50	ns
t _{RVL}	I/O V _L Risettime				400	ns
t _{FVL}	I/O V _L Falltime				60	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V _L)				1000	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V _{CC})				1000	ns
t _{PPSKEW}	Part-to-Part Skew				50	nS
MDR	Maximum Data Rate		2			Mb/s

5. Typical values are for $V_{CC} = +3.3 \text{ V}$, $V_L = +1.8 \text{ V}$ and $T_A = +25^\circ\text{C}$.6. All units are production tested at $T_A = +25^\circ\text{C}$. Limits over the operating temperature range are guaranteed by design.

NLSX4373

TEST SETUPS

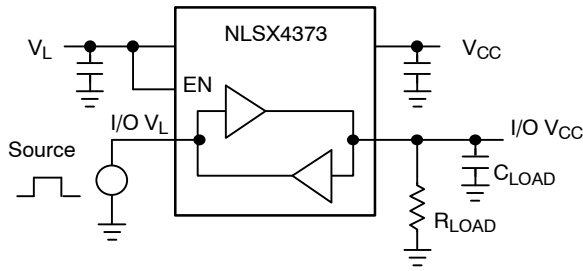


Figure 2. Rail-to-Rail Driving I/O V_L

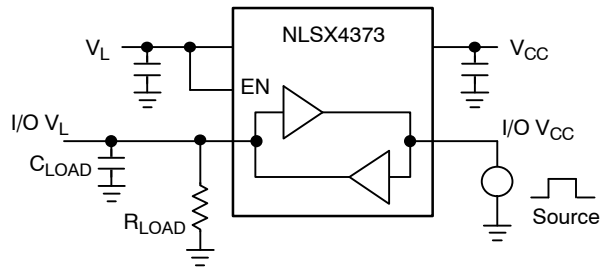


Figure 3. Rail-to-Rail Driving I/O V_{CC}

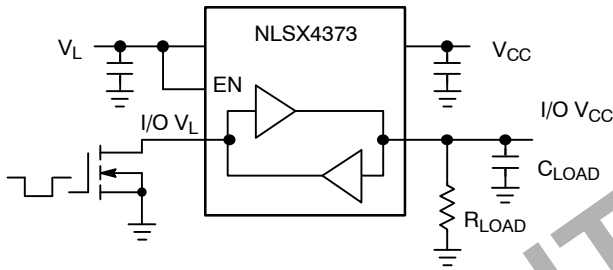


Figure 4. Open-Drain Driving I/O V_L

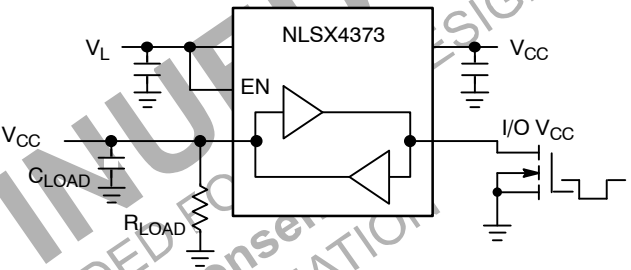


Figure 5. Open-Drain Driving I/O V_{CC}

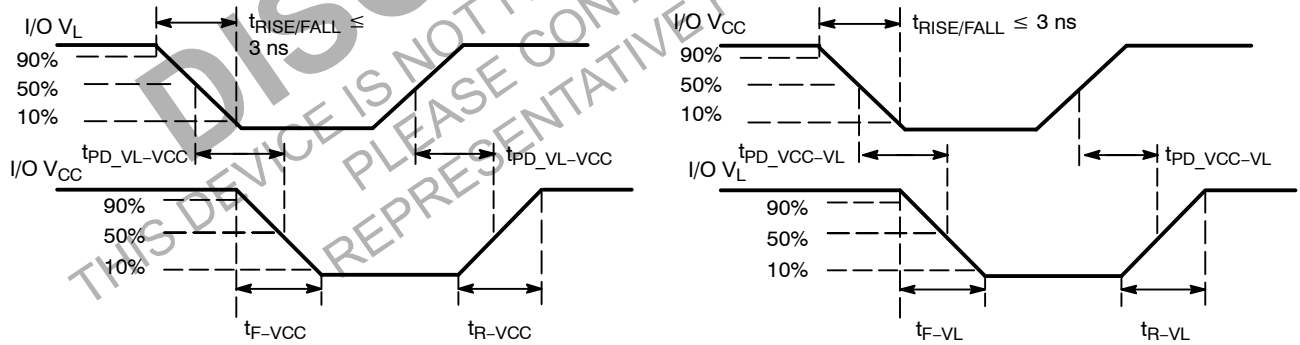
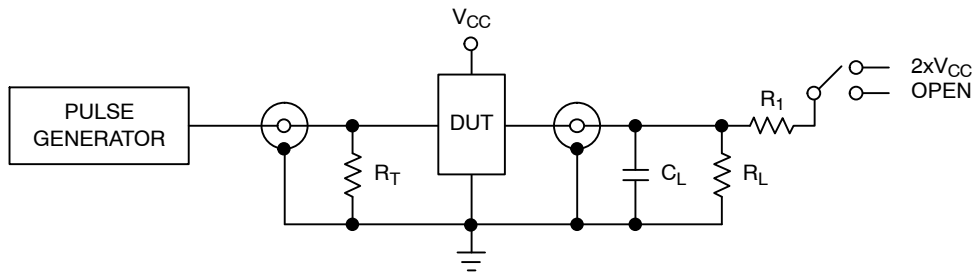


Figure 6. Definition of Timing Specification Parameters



Test	Switch
t_{PZH} , t_{PHZ}	Open
t_{PZL} , t_{PLZ}	$2 \times V_{CC}$

$C_L = 15 \text{ pF}$ or equivalent (Includes jig and probe capacitance)
 $R_L = R_1 = 50 \text{ k}\Omega$ or equivalent
 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

Figure 7. Test Circuit for Enable/Disable Time Measurement

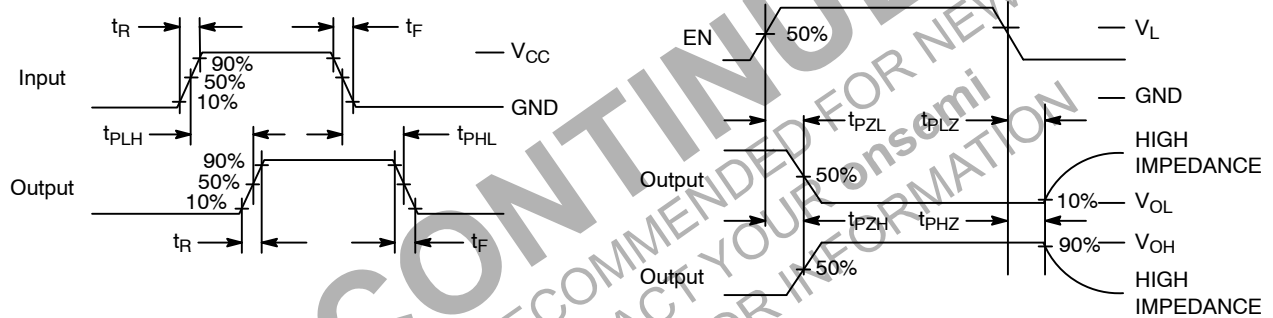


Figure 8. Timing Definitions for Propagation Delays and Enable/Disable Measurement

APPLICATIONS INFORMATION

Level Translator Architecture

The NLSX4373 auto sense translator provides bi-directional voltage level shifting to transfer data in multiple supply voltage systems. This device has two supply voltages, V_L and V_{CC} , which set the logic levels on the input and output sides of the translator. When used to transfer data from the V_L to the V_{CC} ports, input signals referenced to the V_L supply are translated to output signals with a logic level matched to V_{CC} . In a similar manner, the V_{CC} to V_L translation shifts input signals with a logic level compatible to V_{CC} to an output signal matched to V_L .

The NLSX4373 consists of two bi-directional channels that independently determine the direction of the data flow without requiring a directional pin. The one-shot circuits are used to detect the rising or falling input signals. In addition, the one shots decrease the rise and fall time of the output signal for high-to-low and low-to-high transitions.

Each input/output channel has an internal 10 k Ω pull. The magnitude of the pullup resistors can be reduced by connecting external resistors in parallel to the internal 10 k Ω resistors.

Input Driver Requirements

The rise (t_R) and fall (t_F) timing parameters of the open drain outputs depend on the magnitude of the pull-up resistors. In addition, the propagation times (t_{PD}), skew (t_{PSKEW}) and maximum data rate depend on the impedance of the device that is connected to the translator. The timing

parameters listed in the data sheet assume that the output impedance of the drivers connected to the translator is less than 50 k Ω .

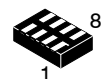
Enable Input (EN)

The NLSX4373 has an Enable pin (EN) that provides tri-state operation at the I/O pins. Driving the Enable pin to a low logic level minimizes the power consumption of the device and drives the I/O V_{CC} and I/O V_L pins to a high impedance state. Normal translation operation occurs when the EN pin is equal to a logic high signal. The EN pin is referenced to the V_L supply and has Overvoltage Tolerant (OVT) protection.

Power Supply Guidelines

During normal operation, supply voltage V_L can be greater than, less than or equal to V_{CC} . The sequencing of the power supplies will not damage the device during the power up operation.

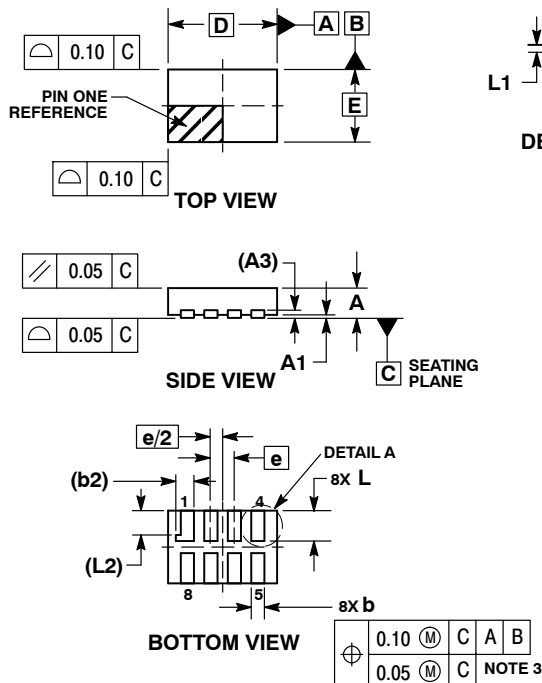
For optimal performance, 0.01 μ F to 0.1 μ F decoupling capacitors should be used on the V_L and V_{CC} power supply pins. Ceramic capacitors are a good design choice to filter and bypass any noise signals on the voltage lines to the ground plane of the PCB. The noise immunity will be maximized by placing the capacitors as close as possible to the supply and ground pins, along with minimizing the PCB connection traces.



SCALE 4:1

UDFN8 1.8x1.2, 0.4P
CASE 517AJ
ISSUE O

DATE 08 NOV 2006

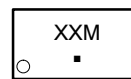


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL TIP.
4. MOLD FLASH ALLOWED ON TERMINALS ALONG EDGE OF PACKAGE. FLASH MAY NOT EXCEED 0.03 ONTO BOTTOM SURFACE OF TERMINALS.
5. DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.127 REF	
b	0.15	0.25
b2	0.30 REF	
D	1.80 BSC	
E	1.20 BSC	
e	0.40 BSC	
L	0.45	0.55
L1	0.00	0.03
L2	0.40 REF	

GENERIC
MARKING DIAGRAM*



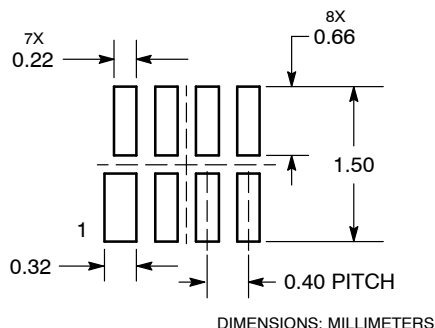
XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

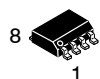
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

MOUNTING FOOTPRINT
SOLDERMASK DEFINED



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DESCRIPTION:	UDFN8 1.8X1.2, 0.4P	PAGE 1 OF 1

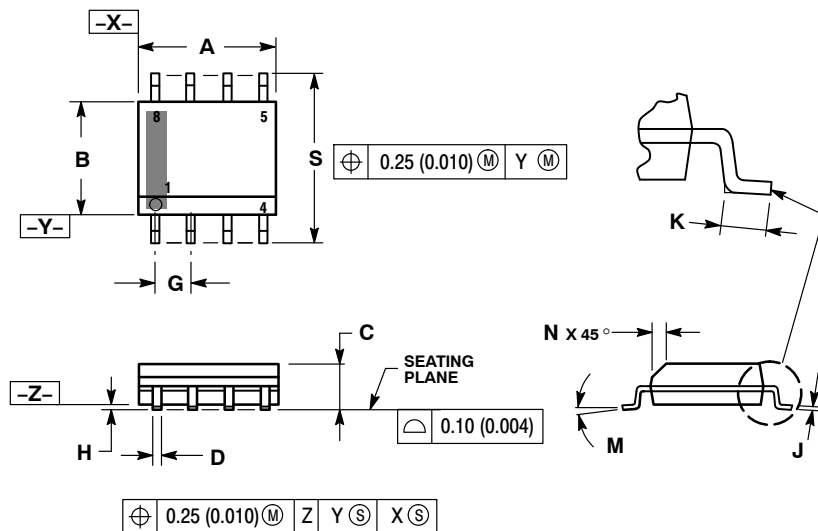
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SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

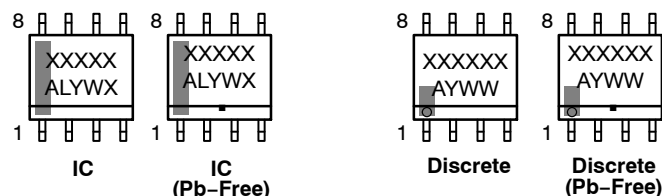
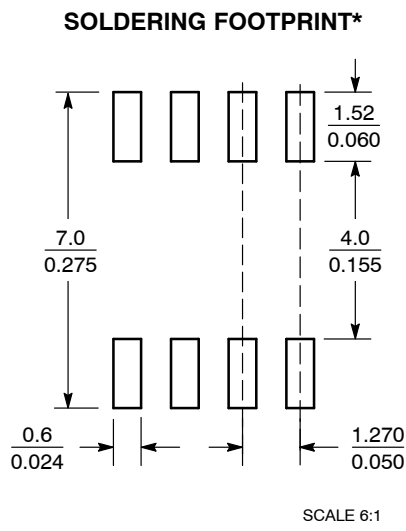


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC
MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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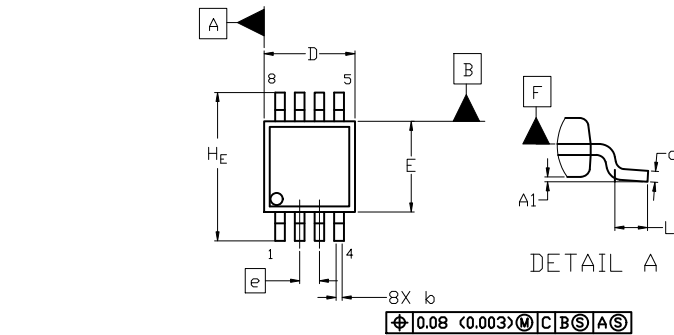
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SCALE 2:1

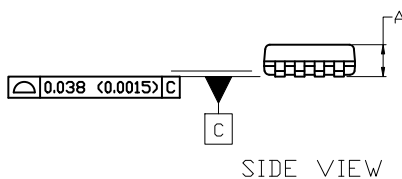
Micro8
CASE 846A-02
ISSUE K

DATE 16 JUL 2020

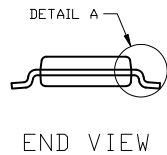


TOP VIEW

NOTE 3

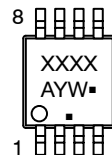


SIDE VIEW



END VIEW

GENERIC
MARKING DIAGRAM*



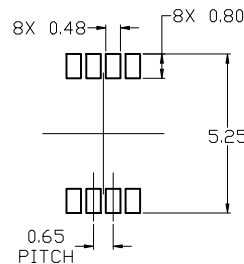
XXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



RECOMMENDED
MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM-10.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
c	0.13	0.18	0.23
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.65 BSC		
H _E	4.75	4.90	5.05
L	0.40	0.55	0.70

STYLE 1:

- PIN 1. SOURCE
- SOURCE
- SOURCE
- GATE
- DRAIN
- DRAIN
- DRAIN
- DRAIN

STYLE 2:

- PIN 1. SOURCE 1
- GATE 1
- SOURCE 2
- GATE 2
- DRAIN 2
- DRAIN 2
- DRAIN 1
- DRAIN 1

STYLE 3:

- PIN 1. N-SOURCE
- N-GATE
- P-SOURCE
- P-GATE
- P-DRAIN
- P-DRAIN
- N-DRAIN
- N-DRAIN

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